

CdTe and HgTe doped with V, Cr, and Mn – prospects for the quantum anomalous Hall effect

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Using first principle calculations we examine properties of (Cd,V)Te, (Cd,Cr)Te, (Hg,V)Te, and (Hg,Cr)Te relevant to the quantum anomalous Hall effect (QAHE), such as the position of V- and Cr-derived energy levels and the exchange interactions between magnetic ions. We consider CdTe and HgTe, containing 12.5% of cation-substitutional V or Cr ions in comparison to the well-known case of (Cd,Mn)Te and (Hg,Mn)Te, and examine their suitability for fabrication of ferromagnetic barriers or ferromagnetic topological quantum wells, respectively. To account for the strong correlation of transition metal d electrons we employ hybrid functionals with different mixing parameters a_{HSE} focusing on $a_{\text{HSE}} = 0.32$, which better reproduces the experimental band gaps in HgTe and $\text{Hg}_{0.875}\text{Mn}_{0.125}\text{Te}$. We find that Cr, like Mn, acts as an isoelectronic dopant but V can be an in-gap donor in CdTe and a resonant donor in HgTe, similar to the case of Fe in HgSe. From the magnetic point of view, Cr-doping results in a ferromagnetic phase within the general gradient approximation (GGA) but interactions become antiferromagnetic within hybrid functionals. However, (Hg,V)Te is a ferromagnet within both exchange-correlation functionals in a stark contrast to (Hg,Mn)Te for which robust antiferromagnetic coupling is found theoretically and experimentally. Furthermore, we establish that the Jahn-Teller effect is relevant only in the case of Cr-doping. Considering lower defect concentrations in HgTe-based quantum wells compared to $(\text{Bi,Sb})_3\text{Te}_2$ layers, our results imply that HgTe quantum wells or (Cd,Hg)Te barriers containing either V or Cr show advantages over $(\text{Bi,Sb,Cr,V})_3\text{Te}_2$ -based QAHE systems but whether (i) ferromagnetic coupling will dominate in the Cr case and (ii) V will not introduce too many electrons to the quantum well is to be checked experimentally.

I. INTRODUCTION

The theoretical prediction [1] and the experimental discovery of the quantum anomalous Hall effect (QAHE) in dilute ferromagnetic semiconductor $(\text{Bi,Sb,Cr})_2\text{Te}_3$ [2] and other systems [3] have triggered research on the prospects of dissipationless and spin-polarized carrier channels for energy-efficient and decoherence-free electronic and spintronic classical and quantum devices [4, 5]. Simultaneously, the application potential of the QAHE for resistance [6–8] and current [9] standards operating in the absence of an external magnetic field has been demonstrated. It has, however, become clear that relatively large native defect concentrations in $(\text{Bi,Sb})_2\text{Te}_3$ and related systems, typically above 10^{19} cm^{-3} , and the associated in-gap impurity-band charge transport, limit the standards' operation to below 100 mK and $1\text{ }\mu\text{A}$ [6–10]. Particularly relevant for the present work is the observation of the QAHE in $(\text{Bi,Sb})_2\text{Te}_3$ layers sandwiched between ferromagnetic $(\text{Zn,Cr})\text{Te}$ barriers [11].

It is, therefore, interesting to consider the metrology prospects of HgTe and related systems, in which the native defect concentration is at the 10^{16} cm^{-3} level [12, 13]. It was found that at the quantum well (QW) thickness corresponding to the topological phase transition, the quantum Hall (QH) plateau $R_{xy} = -h/e^2$ appears in weak magnetic fields and persists in a broad magnetic

range of the magnetic fields [14, 15], the observation relevant to the QHE metrology [15]. The effect is particularly spectacular in the case of $(\text{Cd,Hg})\text{Te}/(\text{Hg,Mn})\text{Te}$ QW, where the broad plateau begins at 50 mT [16]. Those surprising observations were explained by an energetic overlap of the acceptor impurity band with the hole portion of the QW Dirac cone [12, 13]. The Coulomb gap, charge ordering, and the formation of bound magnetic polarons (in the Mn-doped samples) are the essential ingredients of the model [12, 13]. In the case of the studied samples [16], QHE dominates over a possible QAHE [17], as the QAHE requires also the presence of a magnetic field – ferromagnetic coupling between Mn spins in II-VI compounds appears only if the hole density exceeds 10^{20} cm^{-3} [18, 19], whereas intrinsic Mn-Mn interactions are antiferromagnetic [20].

In the present and companion paper [21], we address the question of which cation-substitutional transition-metal (TM) impurities in barriers or QWs could lead to the QAHE in HgTe-based systems. The conditions to be considered experimentally and theoretically include:

1. Sufficiently high – in a couple of percent range – solubility limits of particular dopants at the cation-substitutional positions and without aggregation. Importantly, the equilibrium limits can often be overcome by appropriate growth protocols [22] and, for instance, incorporation of Cr to ZnTe by low-temperature molecular beam epitaxy appears successful [11].

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2. Ferromagnetic coupling between localized spins. We anticipate that Mn and Co dopants can be excluded, as antiferromagnetic superexchange dominates for these ions in II-VI compounds, also in the case of $\text{Hg}_{1-x}\text{Mn}_x\text{Te}$ [20]. Similarly, Fe impurities do not appear appropriate, as they exhibit Van Vleck's paramagnetism in HgTe [23]. Guided by the early theoretical prediction on the ferromagnetic superexchange in Cr-doped II-VI compounds [24] as well by the observation of ferromagnetism at low temperatures in $\text{Zn}_{1-x}\text{Cr}_x\text{Te}$ [11], we consider the Cr and V case.
3. Sufficiently high Curie temperature T_C at x small enough in the case of QW doping to prevent a transition to the topologically trivial phase. In the case of $\text{Hg}_{1-x}\text{Mn}_x\text{Te}$, the inverted band structure disappears at $x_c \simeq 7\%$ [25] but QW confinement shifts x_c to lower values [16]. However, higher TM doping is possible in the case of barriers.
4. Isoelectronic character of TM impurities, as charge doping by magnetic ions will hamper shifting of the Fermi level to the QW gap. The internal reference rule [26], together with the known valence band offsets [27–29] and the positions of V levels in CdTe [30] and Cr levels in CdTe [31] and ZnTe [32] suggest that the relevant $\text{TM}^{2+/3+}$ donor level resides in the HgTe conduction and valence band, respectively. This indicates that V in either (Cd,Hg)Te barriers or HgTe QWs might act as an electron dopant, while Cr as an isoelectronic impurity.
5. Formation of a single chiral edge channel in the presence of spin-polarized magnetic ions. According to the pioneering theoretical analysis [17], the QAHE shows up in magnetically-doped HgTe quantum wells if $p = -\alpha/\beta \gtrsim 0.25$, where $\alpha > 0$ and $\beta < 0$ are the s - d and p - d exchange integrals, respectively. As discussed in the companion paper [21], this condition can be relaxed by tilting the magnetization vector away from the growth direction, as in such a magnetization orientation, spin-orbit interaction diminishes spin-splitting of heavy-hole-like subbands and reduces an effective $|\beta|$ value.
6. Single-ion magnetic anisotropy. Except for Mn^{2+} for which orbital momentum is zero, magnetic ions such as V^{2+} and Cr^{2+} exhibit sizable single-ion anisotropy enlarged by the Jahn-Teller distortion. Accordingly, properties of HgTe QWs with those dopants are expected to be more sensitive to epitaxial strain than (Hg,Mn)Te QWs.

In this paper, we exploit a range of *ab initio* methods to assess three aspects of HgTe doped with 12.5% of cation-substitutional V and Cr ions. First, the concentration of V and Cr opens the band gap in (Hg,TM)Te. As mentioned, in the case of $\text{Hg}_{1-x}\text{Mn}_x\text{Te}$, the transition

between the topological and non-topological phase occurs for $x_c = 0.07$ but we find that x_c can be larger for V and Cr.

Second, the positions of states brought about by V and Cr ions in CdTe and HgTe in comparison to the better-known case of Mn doping. Our results indicate that V impurities, in agreement with experimental results, act as mid-gap donors in CdTe but are close to the bottom of the conduction band in HgTe, so their isoelectronic character has to be checked experimentally. In contrast, Cr impurities do not provide carriers, as the relevant donor state is close to the valence band maximum in CdTe and deeper in the valence band of HgTe. However, compared to the Mn case, Cr donor level is much closer to the Fermi energy resulting in a relatively high magnitude of the p - d exchange integral $|\beta|$ compared to the (Hg,Mn)Te value.

Third, the magnitudes and signs of coupling between magnetic ions in those systems. We conclude that ferromagnetism dominates in the case of V ions, whereas there is a competition between ferromagnetic and anti-ferromagnetic coupling in the case of neighbor Cr spins.

II. COMPUTATIONAL DETAILS

In order to describe properly the band gap and strong correlation of electrons in the TM d bands, we have used the Heyd-Scuseria-Ernzerhof 2006 (HSE06) hybrid functional[33]. The mixing parameter is often set to around 0.20-0.30, and the value $a_{\text{HSE}} = 0.25$ was used for Co-doped CdTe [34]. Other II-IV semiconductors have been studied with a_{HSE} up to 0.36 [35, 36]. We have carried out computations for $a_{\text{HSE}} = 0.25, 0.32,$ and 0.5 with spin-orbit coupling (SOC) taken into account. Guided by our results presented in Sec. III and Appendix A, we focus on data for $a_{\text{HSE}} = 0.32$, which reproduces with accuracy of 0.1 eV experimental band gaps of CdTe, HgTe, $\text{Cd}_{0.875}\text{Mn}_{0.125}\text{Te}$, and $\text{Hg}_{0.875}\text{Mn}_{0.125}\text{Te}$. We have performed the band structure calculations using a plane-wave energy cutoff of 400 eV and an $8 \times 8 \times 8$ k -points grid centered in Γ with 512 k -points in the Brillouin zone, adopting the experimental lattice parameters, $a_0 = 6.46152 \text{ \AA}$ for HgTe and 6.4815 \AA for CdTe [37] and considering cation-substitutional transition metal content of 12.5% for all the compounds investigated. We put the spin polarization along the [001] direction. The band structure of undoped HgTe obtained with $a_{\text{HSE}} = 0.32$ is shown in Fig. 1. For comparison, we have also performed computations within the GGA $+U$ approach. The obtained results are most similar to those obtained for $a_{\text{HSE}} = 0.25$.

Since V and Cr atoms are distributed periodically in supercells, the V- and Cr-derived states form bands. In reality, for randomly distributed magnetic ions, Anderson-Mott localization will result, at least at low magnetic ion concentrations, in strongly localized band gap levels or resonant states, which have a donor or acceptor character, and correspond to d^n/d^{n-1} or d^n/d^{n+1}

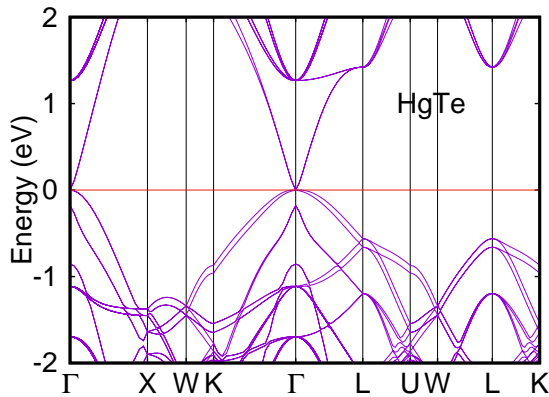


FIG. 1. HSE band structure for HgTe; the value of $a_{\text{HSE}} = 0.32$ has been used.

states, respectively, where $n = 3, 4, 5$ for V, Cr, and Mn, respectively. Furthermore, for the band structure determination, we arrange TM spins ferromagnetically along the [001] direction. Such a TM spins' configuration leads to $sp-d$ exchange splitting of bands, which is \mathbf{k} -dependent due to the interplay of the $sp-d$ exchange with kp and spin-orbit interactions[38].

III. BAND STRUCTURES WITHOUT DISTORTIONS AND PROSPECTS FOR QAHE

We start by showing electronic properties of the CdTe and HgTe doped with V and Cr without taking into account the distortions produced by the structural relaxation and assuming ferromagnetic ordering of TM spins. The band structures obtained within the HSE approach with $a_{\text{HSE}} = 0.32$ for doped CdTe and HgTe with SOC interaction included and for ferromagnetic and periodic spin arrangement in comparison to the Mn-doped CdTe and HgTe are shown in Figs. 2 and 3, respectively. In contrast to the Mn case, where d states are high in the conduction band and deep in the valence band, the states derived from V and Cr d levels reside close to the bottom of the conduction band and the top of the valence band. In accord with experimental observations for CdTe:V [30], the uppermost occupied V-derived donor band in Cd_{0.875}V_{0.125}Te lies in the middle of the band gap and the lowest unoccupied V-derived acceptor band near the bottom of the conduction band. In the case of Cd_{0.875}Cr_{0.125}Te, the occupied Cr-derived d donor bands are strongly hybridized with the host valence band, whereas the Cr unoccupied acceptor band is near the bottom of the conduction band, again in accord with experimental data for CdTe:Cr [31]. A close proximity of the d states to the top of the valence band results in a large magnitude of the $p-d$ exchange integral β and, therefore, in a larger splitting of the topmost valence band subbands near the Γ point of the Brillouin zone in the Cr case compared to Mn doping, the effect

clearly visible in Fig. 2. In accord with experimental results for Hg_{1-x}Mn_xTe, the band gap at the Γ point in a paramagnetic phase, i.e., the distance between the centers of two split conduction subbands and four valence subbands implies normal band ordering with a gap of 0.2 eV. A similar band gap is implied by our results for Hg_{0.875}Cr_{0.125}Te meaning that QWs with Cr concentrations below 10% can show the QAHE. Furthermore, \mathbf{k} -dependent exchange splitting of bands leads to an overlap of the valence and conduction band states for certain \mathbf{k} directions in TM-doped HgTe, which points to the presence of outstanding carrier transport properties in and near the topological regime in those dilute magnetic systems.

Previous extensive studies of dilute magnetic materials [39], together with the results for Hg_{0.815}V_{0.125}Te presented in Fig. 3 for $a_{\text{HSE}} = 0.32$ and also in Appendix A for $a_{\text{HSE}} = 0.25$ and 0.5, indicate that four different scenarios relevant to the QAHE are possible:

1. for certain V concentrations: (i) the band structure remains inverted and (ii) V donor states are in the valence and, therefore, V acts as an isoelectronic impurity, similarly to the case of Mn and, presumably Cr, in HgTe;
2. V forms a resonant state in the conduction band, similarly to the case of Fe in HgSe [40] and Sc in CdSe [41];
3. V acts as an electron dopant but does not give rise to the presence of resonant states;
4. substantial hybridization between V d orbitals and band states leads to unusual band ordering and minigaps in the vicinity of the Fermi energy.

In the case (1), (Hg,V)Te quantum wells can show the QAHE, as—according to our results presented in Sec. V—there is a ferromagnetic interaction between V spins in HgTe. The QAHE could be observed as long the QW is topological, i.e., neither a reduction in the QW thickness nor V doping makes the band ordering topologically trivial. By contrast, within scenarios (2) and (3), it will be difficult to shift the Fermi level from the conduction band to the topological gap for V concentrations sufficiently high to result in a ferromagnetic ground state. Finally, in the fourth case, presumably approximately described by *ab initio* results for Hg_{0.815}V_{0.125}Te with ferromagnetic and periodic spin arrangement (Fig. 3), hybridization between host and dopant states leads to band reconstruction and hybridization gaps. It is unclear on whether the QAHE is possible under these conditions. Finally, we note that V in the (Cd,Hg,V)Te/HgTe quantum wells may act as a modulation electron dopant.

Another situation occurs in (Hg,Cr)Te QWs or (Cd,Hg,Cr)Te barriers, where the Cr donor-like d states reside in the valence band but closer to the Γ_8 point compared to the Mn case. Accordingly, we expect Cr to be an isoelectronic dopant and to generate larger, compared

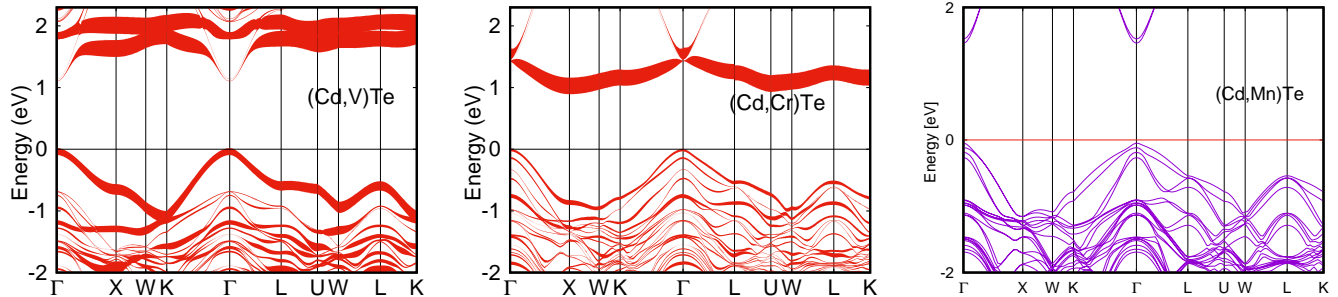


FIG. 2. HSE band structure for $\text{Cd}_{0.875}\text{V}_{0.125}\text{Te}$ and $\text{Cd}_{0.875}\text{Cr}_{0.125}\text{Te}$ in comparison to $\text{Cd}_{0.875}\text{Mn}_{0.125}\text{Te}$, where the Mn donor- and acceptor-like d states are relatively far from the Fermi energy, below the top of the valence band and above the bottom of the conduction band, respectively. The line thickness describes a relative contribution of the V and Cr d states. The Fermi level is set at zero energy and appears to be pinned by the in-gap V donor-like d states. Spins of magnetic ions are ordered ferromagnetically along the [001] direction, which results in a k -dependent exchange spin-splittings of bands. The value of $a_{\text{HSE}} = 0.32$ has been used.

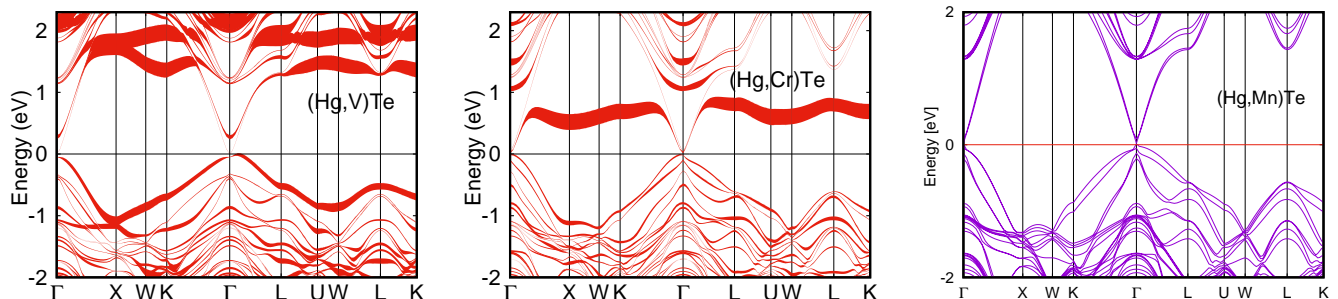


FIG. 3. HSE band structure for $\text{Hg}_{0.875}\text{V}_{0.125}\text{Te}$ and $\text{Hg}_{0.875}\text{Cr}_{0.125}\text{Te}$ in comparison to $\text{Hg}_{0.875}\text{Mn}_{0.125}\text{Te}$, where the Mn donor- and acceptor-like d states are relatively far from the Fermi level, below the top of the valence band and above the bottom of the conduction band, respectively. The line thickness describes a relative contribution of the V and Cr d states. The Fermi level is set at zero energy and appears to be pinned by the V donor-like d states. Spins of magnetic ions are ordered ferromagnetically along the [001] direction, which results in a k -dependent exchange spin-splittings of bands. The value of $a_{\text{HSE}} = 0.32$ has been used.

to Mn doping, exchange splitting of Γ_8 subbands. These large splittings are seen in Fig. 3 which presents computational results for the ferromagnetic arrangement of TM spins along the [001] direction. These results substantiate also the tight-binding model of the (Hg,Cr)Te band structure employed to evaluate the sign and magnitude of exchange interactions between pairs of Cr impurities in HgTe [21]. As tight-binding and *ab initio* results presented in Sec. V point to a competition between antiferromagnetic and ferromagnetic interactions, the observation of the QAHE may require the application of a magnetic field in order to polarize Cr spins.

IV. LOCAL DISTORTIONS PRODUCED BY THE JAHN-TELLER EFFECT

Lattice distortions produced by the Jahn-Teller (JT) effect in zinc-blende II-IV semiconductors are not straightforward. The impurities in $\text{ZnSe}_x\text{S}_{1-x}$ were shown to produce octahedral rotations and changes of bond-angles [42]. Both Cr- and V-doping induce mod-

erate tetrahedral distortions in CdTe and smaller tetrahedral distortions in HgTe. The main effect is a change in the Te-M-Te bond angle. In regular tetrahedra, we have four angles equal to 109.5 degrees. Among these four angles, two remain almost unchanged in the case of doping, one of these angles becomes smaller and another becomes larger. In Fig. 4 we show the crystal structure and the angles that change with the JT distortion.

When we dope the systems with Cr, the angle α becomes larger and β becomes smaller, the opposite happens when we dope with V. This situation is different from what happens in other systems [43, 44], where the two angles α and β become larger or smaller together. This allows a breaking of the degeneracy of the energy levels compatible with the cubic symmetry of the system. Two larger angles or two smaller angles will be more efficient in producing the JT splitting, and they will create a local tetragonal atom arrangement. In Table I, we describe the local distortions in different systems and the gain in the total energy resulting from the JT distortion. These JT distortions help in stabilizing the localized character of states derived from TM d levels.

TABLE I. Bond lengths at 12.5% concentration of magnetic doping. We report the bond connecting the magnetic atoms M (V or Cr) and Te atoms, angles, polyhedral volume (PV), bond angle variance (BAV), distortion index (DI) of the structures with the distortions produced by the Jahn-Teller effect and energy difference between the undistorted E_u and distorted structure E_d . The bonds M-Te₃ and M-Te₄ have equal lengths. α and β are equivalent, if we exchange them the total energy will be the same.

	Cd _{1-x} Cr _x Te	Cd _{1-x} V _x Te	Hg _{1-x} Cr _x Te	Hg _{1-x} V _x Te
Bond length (Å)				
M-Te ₁	2.8019	2.7622	2.8028	2.7282
M-Te ₂	2.8040	2.7520	2.8057	2.7266
M-Te ₃	2.7733	2.7600	2.7589	2.7271
Angles (deg)				
α	102.80	112.60	101.13	109.73
β	115.72	107.64	117.07	109.25
PV(Å ³)	11.053	10.739	10.932	10.409
BAV (deg ²)	43.054	2.794	69.191	0.025
DI (bond length)	0.0040	0.0017	0.0062	0.0002
$E_u - E_d$ (meV)	34.696	4.400	45.05	2 20.094

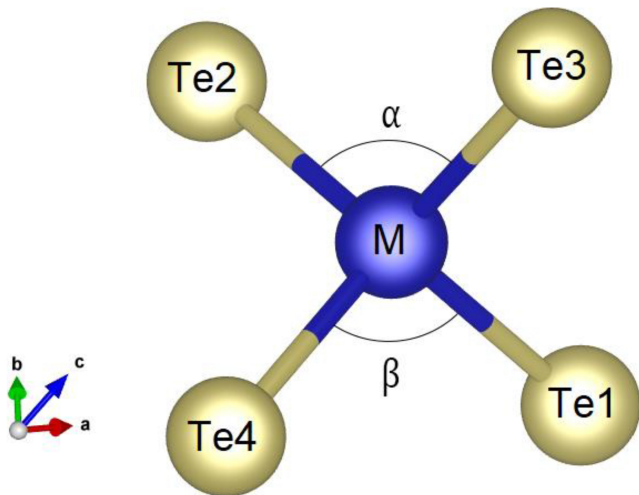


FIG. 4. Angles α and β that change with the Jahn-Teller distortion. In brown Te atoms, in blue the central TM atom (Cr or V).

V. EXCHANGE COUPLINGS BETWEEN TRANSITION METAL SPINS

In this section, we present computational results on exchange couplings between TM spins employing $a_{\text{HSE}} = 0.32$. In Table II, we report energy differences between antiferromagnetic (AFM) and ferromagnetic (FM) configurations of TM spins in CdTe and HgTe doped with V, Cr, and Mn without taking the Jahn-Teller distortion into account. As seen, FM couplings prevail for the V case, whereas the interaction is AFM for Cr- and Mn-doped compounds. Once the Jahn-Teller distortion is taken into account, FM couplings show up in the Cr-compounds, too, as shown in Table III. A comparison of data for $a_{\text{HSE}} = 0.32$ presented here to results obtained for $a_{\text{HSE}} = 0.25$ and 0.50 summarized in Appendix, demonstrate a strong sensitivity of the coupling

TABLE II. Energy differences (meV) between AFM and FM configurations for CdTe and HgTe doped with V, Cr, and Mn ions. ΔE_1 , ΔE_2 and ΔE_3 refer to the first, second, and third neighbors. For all the compounds $a_{\text{HSE}} = 0.32$ has been used. We highlighted in red FM couplings.

compound	ΔE_1	ΔE_2	ΔE_3
Cd _{1-x} V _x Te	-22.3	78.3	-3.4
Cd _{1-x} Cr _x Te	-57.9	-22.6	-1.6
Cd _{1-x} Mn _x Te	-16.2	-16.1	-0.3
Hg _{1-x} V _x Te	35.5	41.2	-2.7
Hg _{1-x} Cr _x Te	-313.4	-150.1	-4.0
Hg _{1-x} Mn _x Te	-17.0	-16.9	-1.6

TABLE III. Energy differences (meV) between AFM and FM configurations of Cr spins obtained without Jahn-Teller (JT) distortion, and with its half and full magnitude for $a_{\text{HSE}} = 0.32$. We highlighted in red FM couplings.

compound	ΔE_1	ΔE_2
Cd _{1-x} Cr _x Te NO JT	-57.9	-22.6
Cd _{1-x} Cr _x Te JT/2	10.4	4.8
Cd _{1-x} Cr _x Te JT	5.9	34.5
Hg _{1-x} Cr _x Te NO JT	-313.4	-150.1
Hg _{1-x} Cr _x Te JT/2	-100.4	-154.4
Hg _{1-x} Cr _x Te JT	-54.8	-231.0

strength to the employed theoretical framework. This sensitivity confirms the presence of a delicate balance between FM and AFM contributions to the TM coupling in the case of early transition metals in II-VI compounds [21].

VI. CONCLUSIONS

According to theoretical studies presented in the present and the companion paper [21], the predicted mag-

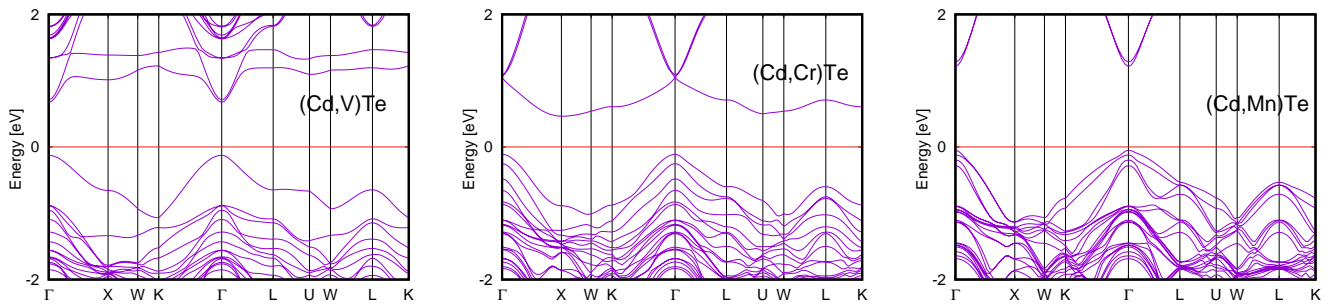


FIG. 5. HSE band structure for $\text{Cd}_{0.875}\text{V}_{0.125}\text{Te}$, $\text{Cd}_{0.875}\text{Cr}_{0.125}\text{Te}$, and $\text{Cd}_{0.875}\text{Mn}_{0.125}\text{Te}$ with ferromagnetic arrangement of TM spins and $a_{\text{HSE}} = 0.25$. The Fermi level is set at zero energy.

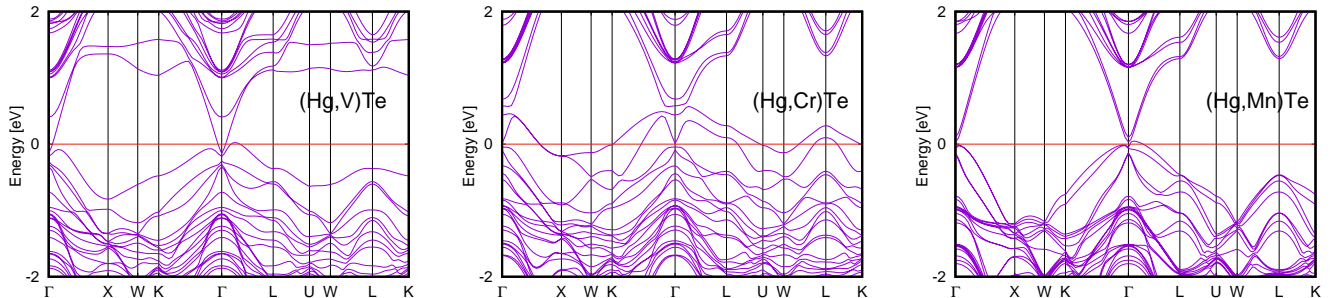


FIG. 6. HSE band structure for $\text{Hg}_{0.875}\text{V}_{0.125}\text{Te}$, $\text{Hg}_{0.875}\text{Cr}_{0.125}\text{Te}$, and $\text{Hg}_{0.875}\text{Mn}_{0.125}\text{Te}$ with ferromagnetic arrangement of TM spins and $a_{\text{HSE}} = 0.25$. The Fermi level is set at zero energy.

nitude and often sign of magnetic coupling between Cr ions in II-VI compounds depends on the approach employed. This fact reflects a competition between ferromagnetic superexchange and mostly antiferromagnetic Bloembergen-Rowland and two-electron terms [21]. Furthermore, according to results presented in Appendix in Fig. 6, pinning of the Fermi level below the top of the valence band by Cr ions in $(\text{Hg,Cr})\text{Te}$ cannot be entirely excluded. Ferromagnetic interactions appear more robust in V-doped compounds, though the donor character of V-impurities may show up in II-VI tellurides.

The ensemble of our results indicates that the most promising strategy for obtaining a QAHE device of HgTe-based systems is to employ $(\text{Cd,Hg,Cr})\text{Te}$ barriers that should be ferromagnetic already above 4.2 K, and in which $sp-d$ exchange splitting of bands should lead to splitting of QW states. That splitting can be further enhanced by a few percent Cr doping of the HgTe QW. However, the observation of the QAHE may require tilting of magnetization away from in-plane or perpendicular orientation [21]. Doping by V is expected to lead to a more robust ferromagnetic ground state but it could be that the resulting electron doping may preclude the shifting of the Fermi level to the topological gap. In any case, a close energetic proximity of d states and the Fermi level opens doors for a new physics in both $(\text{Hg,V})\text{Te}$ and $(\text{Hg,Cr})\text{Te}$, not encountered in the case of $(\text{Hg,Mn})\text{Te}$.

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Appendix A: Transition metal doped compounds with 25% and 50% of the exact exchange

In this Appendix, we present band structures and the magnetic properties for TM-doped CdTe and HgTe obtained employing the hybrid functional with $a_{\text{HSE}} = 0.25$ and $a_{\text{HSE}} = 0.50$ of the exact exchange. The band structure results displayed in Figs. 5, 6, and 7 substantiate the use of $a_{\text{HSE}} = 0.32$ in the main body of the text. In particular, in the case of $\text{Hg}_{0.875}\text{Mn}_{0.125}\text{Te}$, the experimental value of the band gap $E_g = E_{\Gamma_6} - E_{\Gamma_8} = 0.2 \text{ eV}$ [45] is close to the computational data for $a_{\text{HSE}} = 0.32$

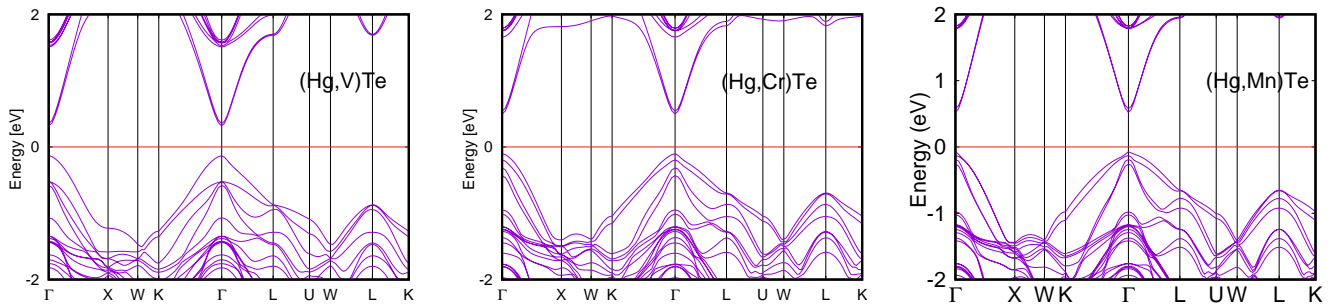


FIG. 7. HSE band structure for $\text{Hg}_{0.875}\text{V}_{0.125}\text{Te}$, $\text{Hg}_{0.875}\text{Cr}_{0.125}\text{Te}$, and $\text{Hg}_{0.875}\text{Mn}_{0.125}\text{Te}$ with ferromagnetic arrangement of TM spins and $a_{\text{HSE}} = 0.5$. The Fermi level is set at zero energy.

TABLE IV. Energy differences (meV) between AFM and FM spin configurations for TM doped CdTe and HgTe. ΔE_1 , ΔE_2 , and ΔE_3 refer to the first, second, and third neighbors. For all compounds, $a_{\text{HSE}} = 0.25$ is used, except for values with asterisks, which have been obtained with $a_{\text{HSE}} = 0.35$, because the calculations with $a_{\text{HSE}} = 0.25$ do not converge in those cases. We have highlighted in red the FM couplings.

compound	ΔE_1	ΔE_2	ΔE_3
$\text{Cd}_{1-x}\text{V}_x\text{Te}$	-38.1	22.8	0.6
$\text{Cd}_{1-x}\text{Cr}_x\text{Te}$	-10.5*	-16.8*	-4.8
$\text{Cd}_{1-x}\text{Mn}_x\text{Te}$	-21.9	-21.8	-0.5
$\text{Hg}_{1-x}\text{V}_x\text{Te}$	47.6	51.5	-1.6
$\text{Hg}_{1-x}\text{Cr}_x\text{Te}$	-77.9	-35.9	-5.1
$\text{Hg}_{1-x}\text{Mn}_x\text{Te}$	-22.3	-22.2	-2.0

(Fig. 3) but E_g is too small and too large for $a_{\text{HSE}} = 0.25$ and 0.5, respectively, as shown in Figs. 6 and 7.

As we can see in Fig. 6, for $a_{\text{HSE}} = 0.25$ we find a metallic phase in the case of HgTe doped with Cr because acceptor d -states of the dopants undergo a shift below the top of the valence band. The band structures obtained within the GGA+ U approach resemble the re-

sults obtained at $a_{\text{HSE}} = 0.25$ for all compounds and, therefore, we do not display them.

In Tables IV and Table V we report the values of the spin-spin couplings for the Cr-doped compounds obtained by using $a_{\text{HSE}} = 0.25$ and 0.5, respectively. In the latter case, we find that HgTe doped with Cr shows ferromagnetic couplings.

TABLE V. Energy differences (meV) between AFM and FM spin configurations with respect to the FM state taking the Jahn-Teller distortion into account for Cr-doped compounds. With JT/2 we indicate that we consider an average of the positions of the atoms without and with the JT distortion. We have highlighted in red the FM couplings. The results have been obtained for $a_{\text{HSE}} = 0.50$.

compound	ΔE_1	ΔE_2
$\text{Cd}_{1-x}\text{Cr}_x\text{Te}$ NO JT	-218.7	-160.3
$\text{Cd}_{1-x}\text{Cr}_x\text{Te}$ JT/2	-62.3	24.1
$\text{Hg}_{1-x}\text{Cr}_x\text{Te}$ NO JT	74.0	7.8
$\text{Hg}_{1-x}\text{Cr}_x\text{Te}$ JT/2	88.6	-22.7

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